



DMTH6010LPSW

60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	Ι _D T _C = +25°C
60V	8mΩ @ V _{GS} = 10V	80A
	12mΩ @ V _{GS} = 4.5V	64.5A

Features

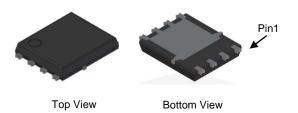
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMTH6010LPSWQ</u>)

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

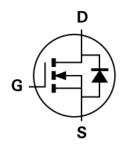
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

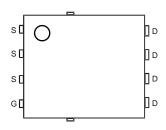
PowerDI5060-8 (SWP) (Type Q)



Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)





Internal Schematic

Top View Pin Configuration

Ordering Information (Note 4)

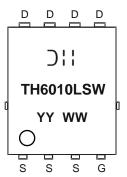
Part Number	Case	Packaging
DMTH6010LPSW-13	PowerDI5060-8 (SWP) (Type Q)	2,500 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



D11 = Manufacturer's Marking
TH6010LSW = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 5) $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		ID	15.5 11	А
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		I _D	80 56	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	320	A	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	80	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle	I _{SM}	320	A	
Avalanche Current, L = 0.1mH	I _{AS}	20	A	
Avalanche Energy, L = 0.1mH		E _{AS}	20	mJ

Thermal Characteristics

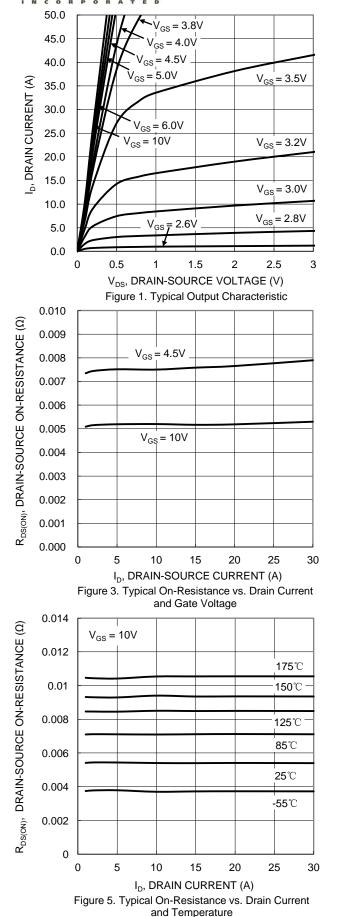
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.9	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	52	°C/W	
Total Power Dissipation (Note 6)	T _C = +25°C	PD	75	W
Thermal Resistance, Junction to Case (Note 6)		R _{0JC}	2.0	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

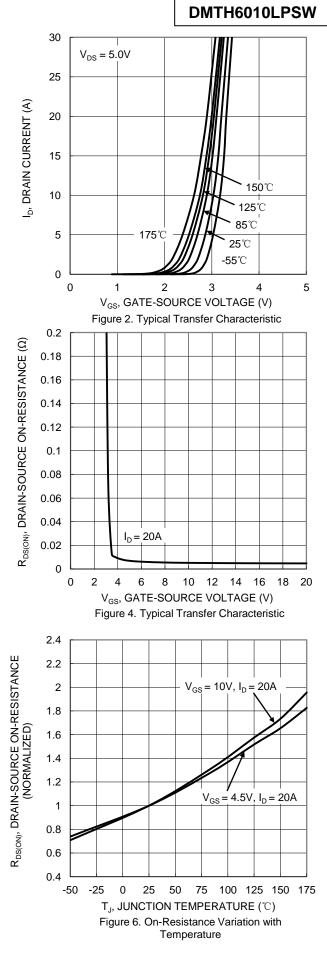
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			-				
	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			1	r		1	
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	—	—	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	P	-	5.3	8	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	7.9	12	1112	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)	·						
Input Capacitance	Ciss	-	2,090	-		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	746	—	pF		
Reverse Transfer Capacitance	Crss	_	38.5	_			
Gate Resistance	Rg	-	0.59	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg		19.3	—			
Total Gate Charge (V _{GS} = 10V)	Qg	_	41.3	—	nC	$V_{DS} = 30V, I_D = 20A$	
Gate-Source Charge	Q _{gs}		6	—	nc		
Gate-Drain Charge	Q _{gd}		8.8	—			
Turn-On Delay Time	t _{D(ON)}		5.7	-		$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 20A, R_g = 3\Omega$	
Turn-On Rise Time	t _R	_	4.3	—			
Turn-Off Delay Time	t _{D(OFF)}	—	23.4	_	ns		
Turn-Off Fall Time	tF	—	9.7	—			
Body Diode Reverse Recovery Time	t _{RR}	_	35.4	—	ns	$I_{-} = 200$ di/dt = 1000/up	
Body Diode Reverse Recovery Charge	Q _{RR}		38.2	—	nC	I _F = 20A, di/dt = 100A/µs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:

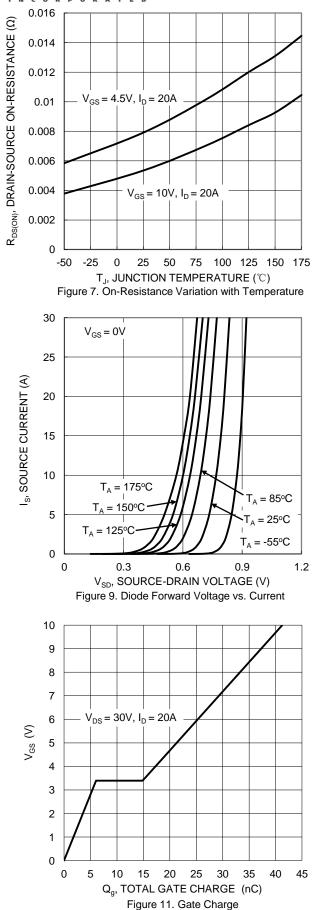


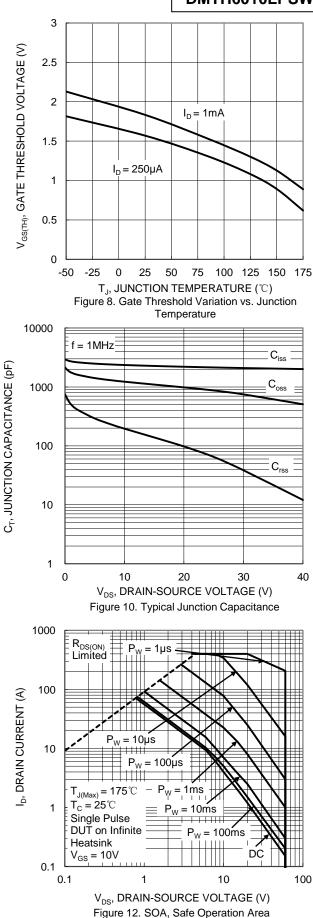




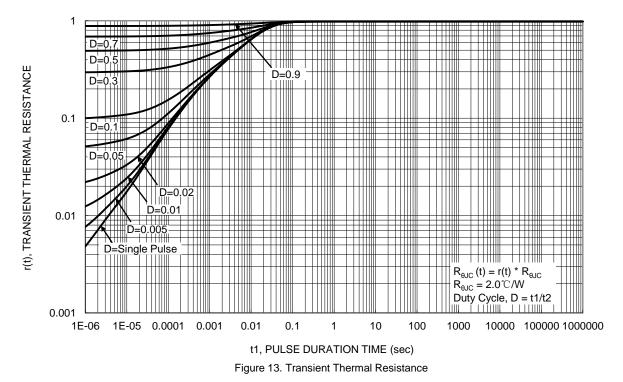










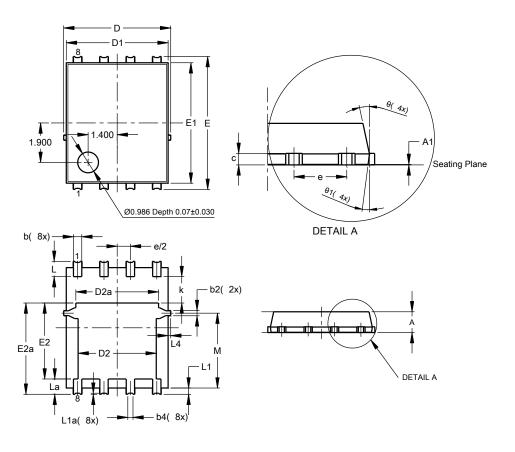




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)

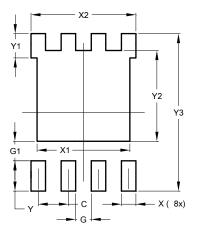


PowerDI5060-8 (SWP) (Type Q)					
Dim	Min Max		Тур		
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF	-		
С	0.230	0.330	0.277		
D		.15 BS(0		
D1	4.70	4.70 5.10 4.9			
D2	3.56	3.96	3.76		
D2a			3.98		
E	6.40 BSC				
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1	.27BSC)		
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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